

Description

The HSH0026 is the high cell density trench N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

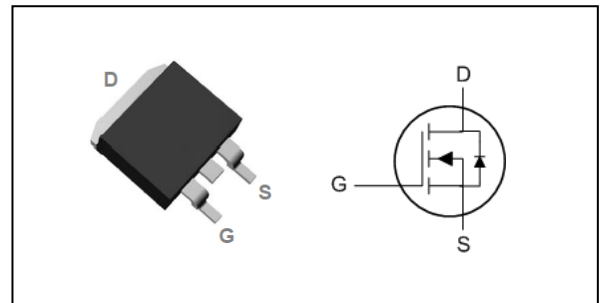
The HSH0026 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	100	V
$R_{DS(ON),typ}$	16	m Ω
I_D	50	A

TO263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	50	A
$I_D@T_C=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	22	A
I_{DM}	Pulsed Drain Current ²	75	A
EAS	Single Pulse Avalanche Energy ³	780	mJ
I_{AS}	Avalanche Current	18	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	62.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹ ($t \leq 10S$)	---	50	$^\circ\text{C/W}$
	Thermal Resistance Junction-ambient ¹ (Steady State)	---	2	$^\circ\text{C/W}$



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.08	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=9A$	---	16	22	$m\Omega$
		$V_{GS}=4.5V$, $I_D=7A$	---	20	28	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.2	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.5	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	10	μA
		$V_{DS}=80V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=9A$	---	28	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	1.6	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=80V$, $V_{GS}=10V$, $I_D=7A$	---	36	---	nC
Q_{gs}	Gate-Source Charge		---	5	---	
Q_{gd}	Gate-Drain Charge		---	10	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=7A$	---	11.5	---	ns
T_r	Rise Time		---	29	---	
$T_{d(off)}$	Turn-Off Delay Time		---	42	---	
T_f	Fall Time		---	18	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1MHz$	---	1930	---	pF
C_{oss}	Output Capacitance		---	245	---	
C_{rss}	Reverse Transfer Capacitance		---	125	---	

Diode Characteristics

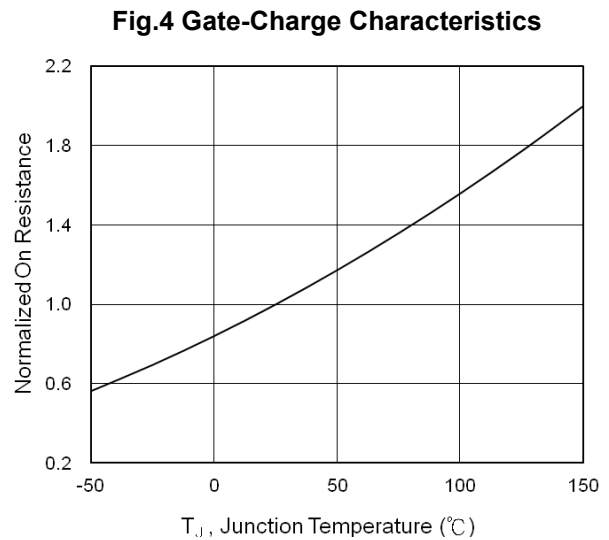
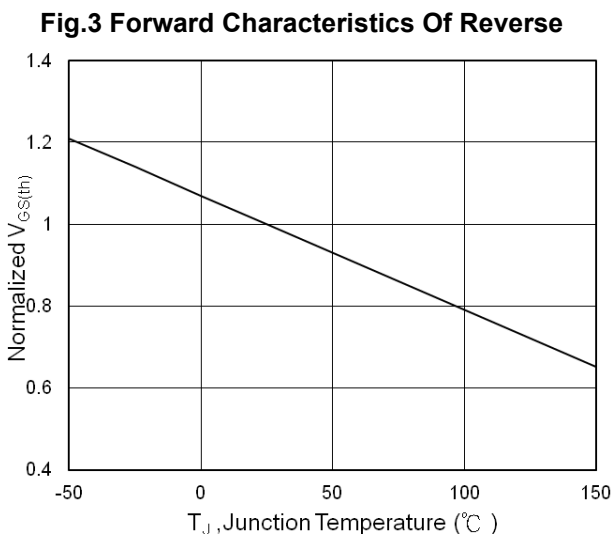
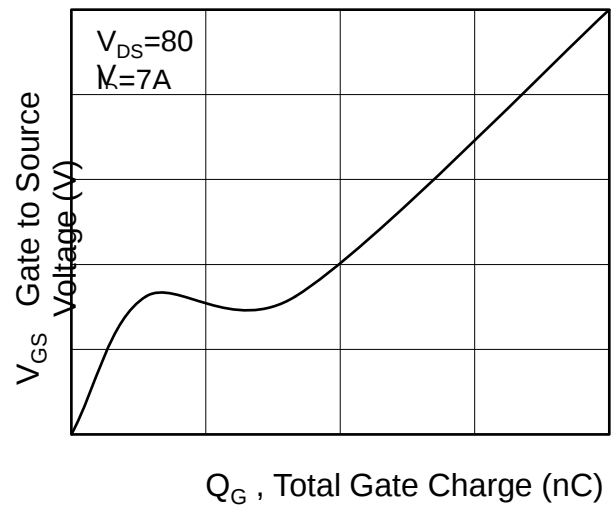
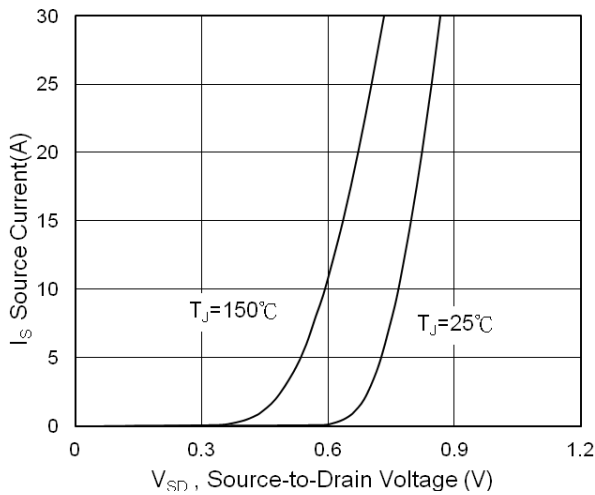
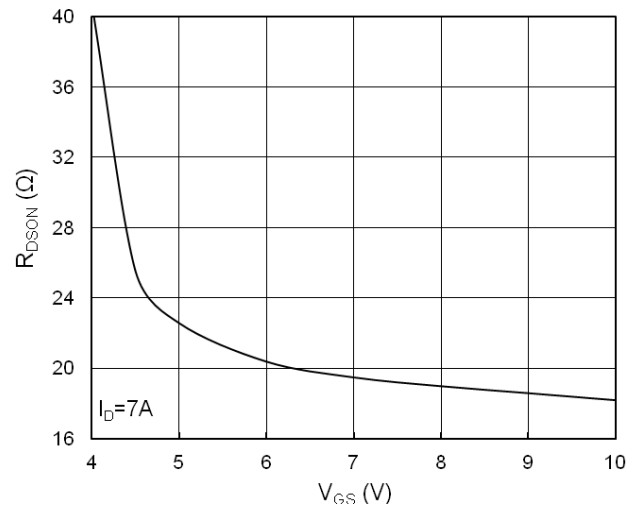
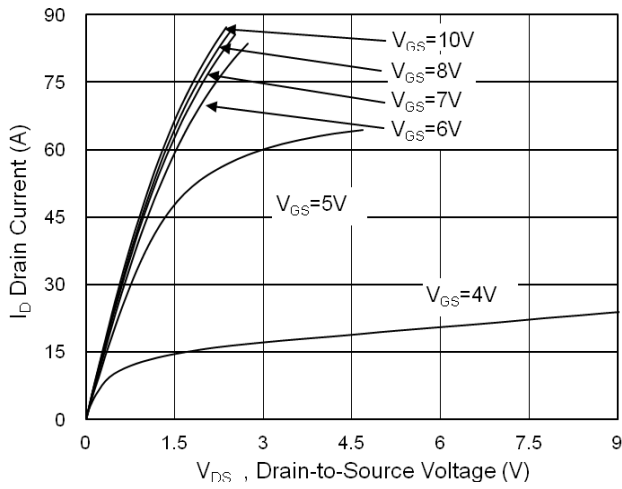
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	---	---	50	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=7A$, $dI/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	48	---	nS
Q_{rr}	Reverse Recovery Charge		---	29	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1mH$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



N-Ch 100V Fast Switching MOSFETs



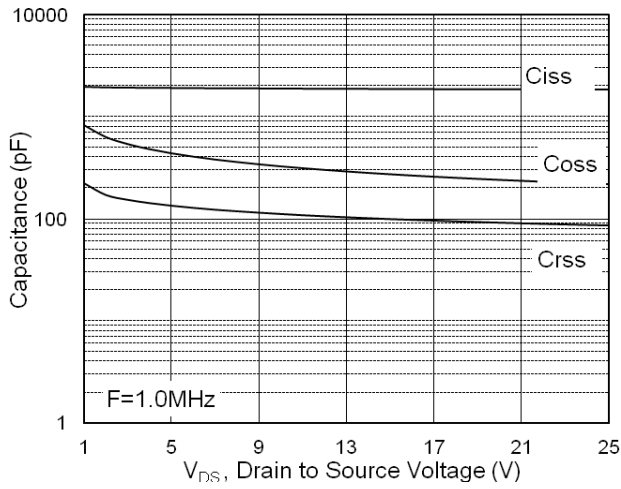


Fig.7 Capacitance

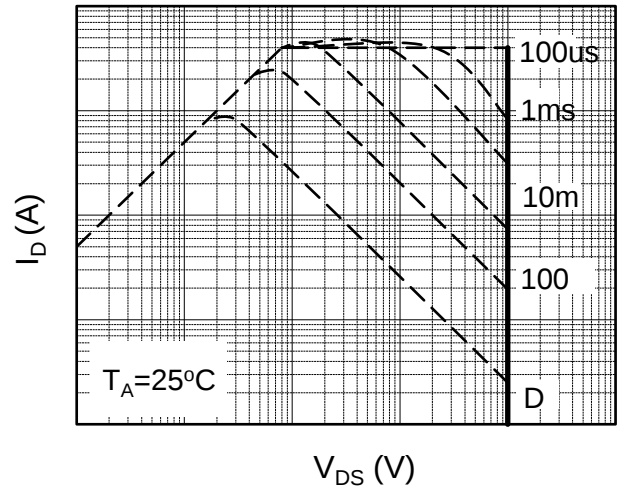


Fig.8 Safe Operating Area

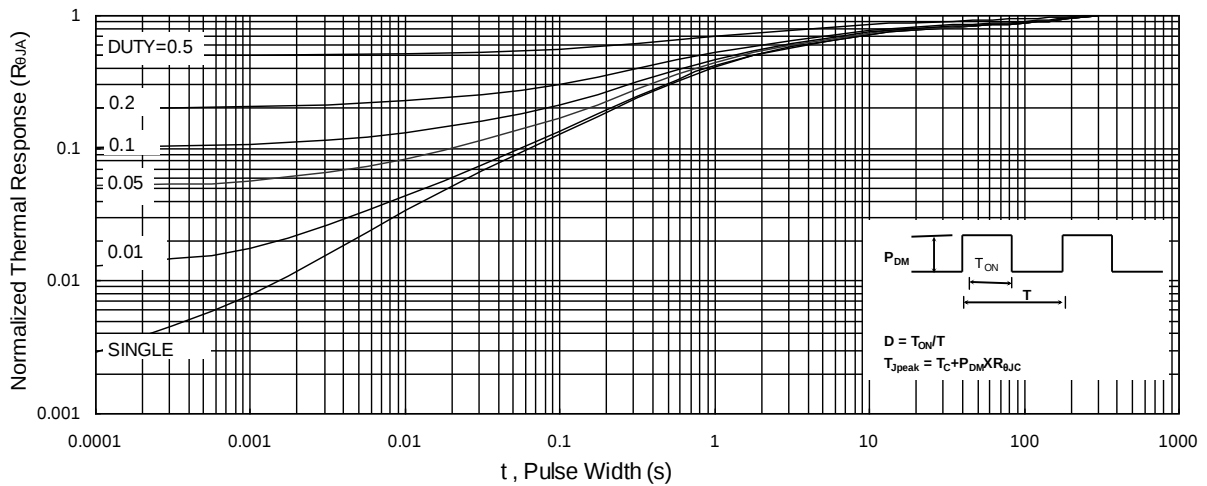


Fig.9 Normalized Maximum Transient Thermal Impedance

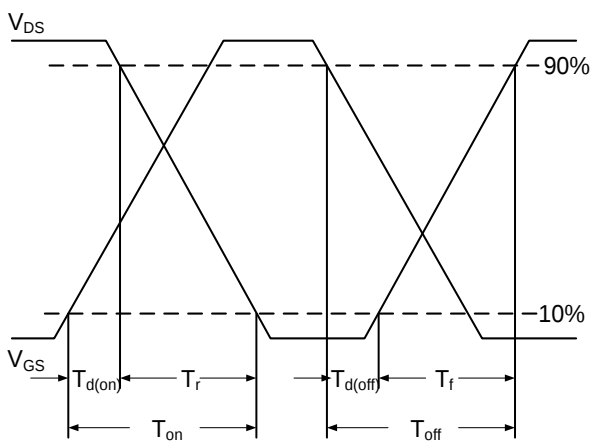


Fig.10 Switching Time Waveform

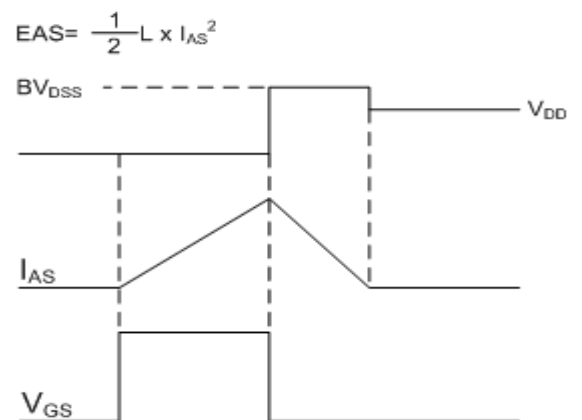


Fig.11 Unclamped Inductive Switching